

isc Silicon NPN Power Transistor

2SC3563

DESCRIPTION

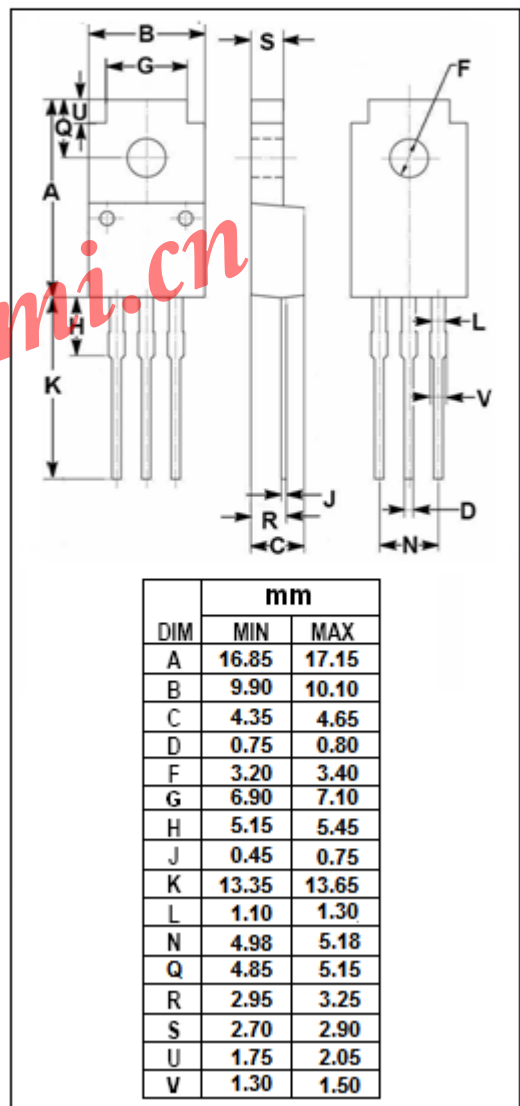
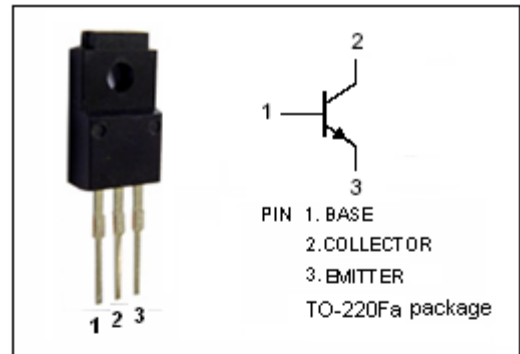
- High Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 450V$  (Min)
- High Switching Speed

APPLICATIONS

- Switching regulator and high voltage switching applications.
- High speed DC-DC converter applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	600	V
$V_{CEO}$	Collector-Emitter Voltage	450	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	10	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	40	W
	Collector Power Dissipation @ $T_a=25^{\circ}C$	2	
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



**isc Silicon NPN Power Transistor****2SC3563****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	450			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	600			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=500\text{V}; I_E=0$			100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			1	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	20			
$h_{FE-2}$	DC Current Gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	8			

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